

## Silicon Planar PNPN Thyristor (4A SCR)

### DESCRIPTION

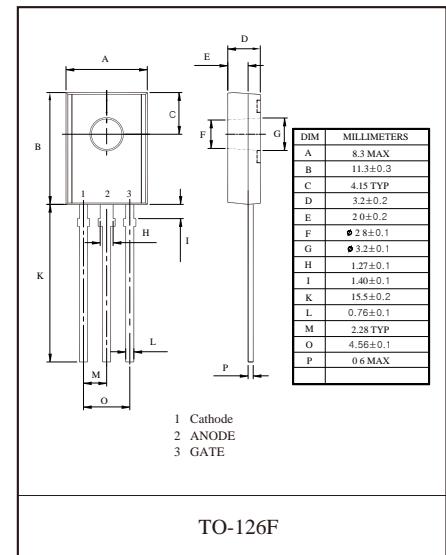
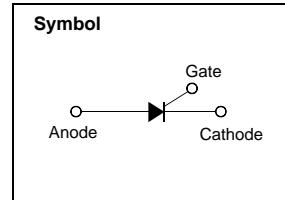
Thyristor in a TO-126F Plastic Package.

### FEATURES

- The consumption level provide reliable applications, such as temperature, lighting, speed, etc.

### APPLICATIONS

- Applied to high Voltage control circuit.



### Absolute Maximum Ratings(T<sub>a</sub>=25°C)

Parameter	Symbol	Test Conditions		Rating	Unit
Repetitive peak off-state voltages	V <sub>DRM</sub> , V <sub>RRM</sub>	R <sub>GK</sub> =1K T <sub>c</sub> =-40~110°C	C106B C106D C106M	200 400 600	V
RMS on-state current	I <sub>T(RMS)</sub>	T <sub>c</sub> =80°C		4	A
Average on-state current	I <sub>T(AV)</sub>	T <sub>c</sub> =80°C		2.55	A
Non-repetitive peak on-state current	I <sub>TSM</sub>	1/2 Cycle, Sine Wave, 60Hz, T <sub>j</sub> =110°C		20	A
I <sup>2</sup> t for fusing	I <sup>2</sup> t	t=8.3ms		1.65	A <sup>2</sup> s
Peak gate power	P <sub>GM</sub>	T <sub>c</sub> =80°C		500	mW
Peak Average power	P <sub>G(AV)</sub>	T <sub>c</sub> =80°C		100	mW
Peak gate current	I <sub>GM</sub>	T <sub>c</sub> =80°C		0.2	A
Junction Temperature	T <sub>j</sub>			-40~+110	°C
Storage Temperature Range	T <sub>stg</sub>			-40~+150	°C

### ELECTRICAL CHARACTERISTICS (T<sub>amb</sub>=25°C unless otherwise specified)

Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
Repetitive peak off-state current	I <sub>DRM</sub> , I <sub>RRM</sub>	V <sub>AK</sub> =Rated V <sub>DRM</sub> or V <sub>RRM</sub> R <sub>GK</sub> =1KΩ	T <sub>c</sub> =25 °C			10	μA
			T <sub>c</sub> =110 °C			100	
On-state voltage	V <sub>TM</sub>	I <sub>TM</sub> =4.0A tp=380uS				2.2	V
Gate trigger current	I <sub>GT</sub>	V <sub>AK</sub> =6.0Vdc R <sub>L</sub> =100Ω	T <sub>c</sub> =25 °C		15	200	μA
			T <sub>c</sub> =-40 °C		35	500	
Gate trigger voltage	V <sub>GT</sub>	V <sub>AK</sub> =6.0Vdc R <sub>L</sub> =100Ω	T <sub>c</sub> =25 °C	0.4	0.60	0.80	V
			T <sub>c</sub> =-40 °C	0.5	0.75	1.00	
Holding current	I <sub>H</sub>	V <sub>AK</sub> =12.0Vdc R <sub>GK</sub> =1KΩ	T <sub>c</sub> =25 °C		0.19	3.0	mA
			T <sub>c</sub> =-40 °C		0.33	6.0	
			T <sub>c</sub> =110 °C		0.07	2.0	
Latching current	I <sub>L</sub>	V <sub>AK</sub> =12.0Vdc I <sub>G</sub> =20mA	T <sub>c</sub> =25 °C		0.20	5.0	mA
			T <sub>c</sub> =-40 °C		0.35	7.0	
Critical rate of rise of off-state voltage	dv/dt	V <sub>AK</sub> =Rated V <sub>DRM</sub> , R <sub>GK</sub> =1KΩ T <sub>c</sub> =110 °C			8.0		V/us

## Typical Characteristics

